

BIPOLAR ANALOG INTEGRATED CIRCUIT UPC2776TB

5 V, SUPER MINIMOLD SILICON RFIC WIDEBAND AMPLIFIER

FEATURES

• WIDE FREQUENCY RESPONSE: 2.7 GHz

FLAT GAIN RESPONSE: ±1.0 dB

• HIGH GAIN: 23 dB

• MEDIUM OUTPUT POWER: P1dB: 6.0 dBm at 1.0 GHz

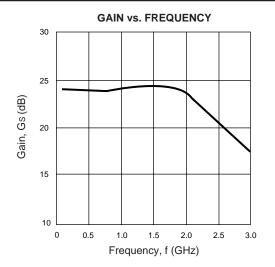
5 V SINGLE SUPPLY VOLTAGE

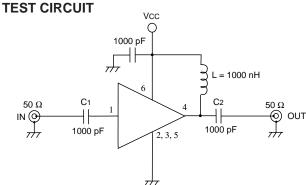
SMALL SURFACE MOUNT PACKAGE: SOT-363

AVAILABLE ON TAPE AND REEL

DESCRIPTION

NEC's UPC2776TB is a Silicon Monolithic integrated circuit which is manufactured using the NESAT™III process. This device is suitable for wide band IF blocks due to its high gain and flat response. The UPC2776TB is pin compatible and has comparable performance as the larger UPC2776T, so it is suitable for use as a replacement to help reduce system size. The IC is housed in a 6 pin super minimold or SOT-363 package. The UPC2776TB is designed as a low cost IC gain stage in DBS, TVRO, PCS, WLAN and other communication receivers.





ELECTRICAL CHARACTERISTICS (Vcc = 5.0 V, TA = 25°C, ZL = Zs = 50 Ω)

	PART NUMBER PACKAGE OUTLINE		UPC2776TB \$06		
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
Icc	Circuit Current (no signal)	mA	18	25	33
Gs	Small Signal Gain, f = 1 GHz	dB	21	23	26
fu	Upper Limit Operating Frequency (The gain at fu is 3 dB down from the gain at 0.1 GHz)	GHz	2.3	2.7	
ΔGs	Gain Flatness, f = 0.1 to 2.0 GHz	dB		±1.0	
P1dB	Output Power at 1 dB Compression, f = 1 GHz	dBm	+4	+6.0	
NF	Noise Figure, f = 1 GHz			6.0	7.5
RLIN	Input Return Loss, f = 1 GHz	dB	4.5	7.5	
RLout	Output Return Loss, f = 1 GHz	dB	15	20	
ISOL	ISOL Isolation, f = 1 GHz		27	32	
Psat	Saturated Output Power, f = 1 GHz	dBm		8.5	
IMз	IM3 3rd Order Intermodulation Distortion, f = 1 GHz Po = 0 dBm each tone, f1 = 1000 MHz, f2 = 1002 MHz			-30	

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Date Published: June 28, 2005

ABSOLUTE MAXIMUM RATINGS¹ (TA = 25°C)

SYMBOLS PARAMETERS		UNITS	RATINGS
Vcc	Supply Voltage	V	6
Icc	Icc Total Circuit Current		60
Pin	Input Power	dBm	+10
Рт	Total Power Dissipation ²	mW	200
Тор	Operating Temperature	°C	-40 to +85
Tstg	Storage Temperature	°C	-55 to +150

Notes:

- Operation in excess of any one of these parameters may result in permanent damage.
- 2. Mounted on a 50 x 50 x 1.6 mm epoxy glass PWB ($T_A = 85$ °C).

RECOMMENDED OPERATING CONDITIONS

SYMBOLS	PARAMETERS	UNITS	MIN	TYP	MAX
Vcc	Supply Voltage	V	4.5	5.0	5.5

ORDERING INFORMATION (Solder Contains Lead)

PART NUMBER	QTY
UPC2776TB-E3	3K/Reel

Note:

Embossed Tape, 8 mm wide. Pins 1, 2 and 3 face perforated side of tape.

ORDERING INFORMATION (Pb-Free)

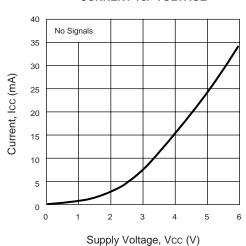
PART NUMBER	QTY
UPC2776TB-E3-A	3K/Reel

Note:

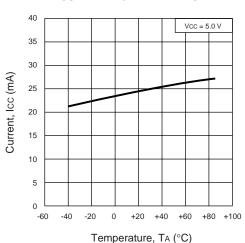
Embossed Tape, 8 mm wide. Pins 1, 2 and 3 face perforated side of tape.

TYPICAL PERFORMANCE CURVES (TA = 25°C)

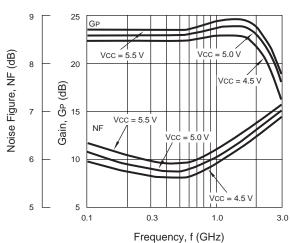




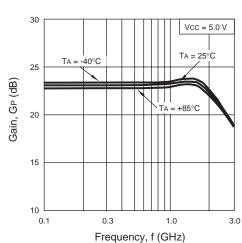
CURRENT vs. TEMPERATURE



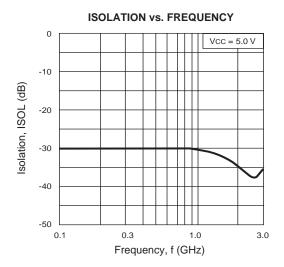
NOISE FIGURE AND GAIN vs. FREQUENCY and VOLTAGE



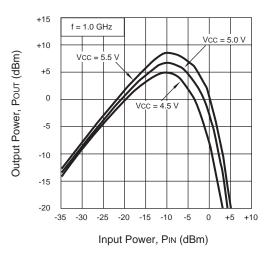
GAIN vs. FREQUENCY and TEMPERATURE



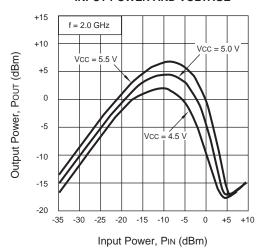
TYPICAL PERFORMANCE CURVES (TA = 25° C)



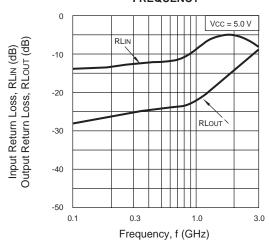
OUTPUT POWER vs. INPUT POWER AND VOLTAGE



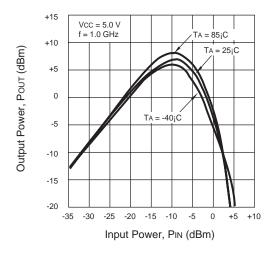
OUTPUT POWER vs.
INPUT POWER AND VOLTAGE



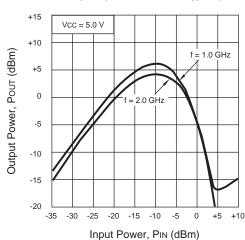
INPUT, OUTPUT RETURN LOSS vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER AND TEMPERATURE

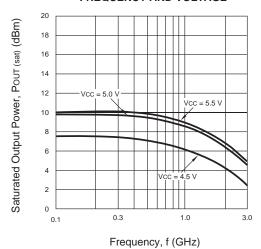


OUTPUT POWER vs. INPUT POWER AND FREQUENCY

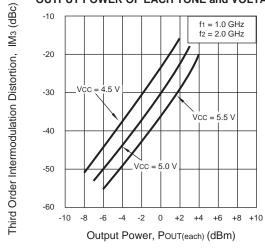


TYPICAL PERFORMANCE CURVES (TA = 25° C)

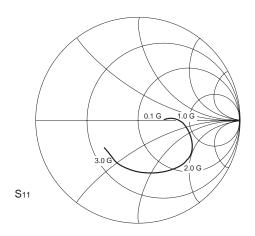
SATURATED OUTPUT POWER vs. FREQUENCY AND VOLTAGE

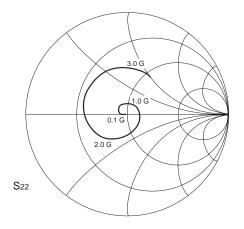


THIRD ORDER INTERMODULATION DISTORTION vs. OUTPUT POWER OF EACH TONE and VOLTAGE



TYPICAL SCATTERING PARAMETERS (TA = 25°C)





UPC2776TB

Vcc = Vout = 5.0 V, Icc = 27 mA

EQUENCY		S11	s	21	S ₁	12	S22		K
GHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG	
0.1	0.226	2.8	13.844	-5.9	0.029	-1.5	0.032	-177.4	1.39
0.2	0.240	6.4	13.862	-12.5	0.029	0.3	0.024	-171.9	1.39
0.3	0.254	10.4	13.942	-18.6	0.028	3.2	0.030	-176.3	1.40
0.4	0.267	11.4	14.123	-25.2	0.029	4.8	0.031	-167.6	1.36
0.5	0.285	11.1	14.267	-31.8	0.029	7.2	0.037	-167.3	1.33
0.6	0.308	8.5	14.423	-38.6	0.029	9.3	0.038	-159.3	1.28
0.7	0.345	6.1	14.670	-45.5	0.030	10.7	0.040	-160.7	1.22
0.8	0.386	3.9	14.864	-52.8	0.030	11.0	0.043	-161.9	1.18
0.9	0.425	1.4	15.210	-60.1	0.031	11.9	0.055	-169.0	1.12
1.0	0.449	-1.5	15.455	-68.4	0.030	11.7	0.072	-169.1	1.10
1.1	0.466	-6.1	15.564	-76.6	0.030	10.6	0.084	-169.1	1.08
1.2	0.478	-12.0	15.550	-84.9	0.030	11.7	0.093	-173.6	1.07
1.3	0.507	-17.7	15.622	-93.1	0.030	13.4	0.094	177.9	1.05
1.4	0.533	-24.7	15.577	-101.3	0.029	13.2	0.114	167.0	1.05
1.5	0.564	-30.3	15.527	-110.6	0.029	13.5	0.130	164.1	1.02
1.6	0.568	-36.4	15.285	-119.0	0.027	11.3	0.154	158.0	1.07
1.7	0.576	-42.0	14.960	-127.8	0.026	12.6	0.167	152.6	1.09
1.8	0.571	-48.5	14.570	-136.4	0.024	14.8	0.179	143.0	1.18
1.9	0.570	-54.5	14.026	-144.7	0.023	15.8	0.196	135.2	1.27
2.0	0.569	-59.7	13.715	-151.7	0.022	18.2	0.212	128.1	1.35
2.1	0.564	-64.2	13.283	-159.8	0.020	23.5	0.228	121.6	1.48
2.2	0.548	-69.6	12.926	-167.5	0.018	27.1	0.240	115.9	1.66
2.3	0.535	-75.5	12.515	-174.8	0.018	36.3	0.251	108.1	1.75
2.4	0.516	-81.8	12.093	177.9	0.016	41.9	0.268	102.4	2.01
2.5	0.515	-87.0	11.498	170.1	0.017	53.3	0.279	96.0	1.99
2.6	0.508	-90.9	11.136	163.1	0.015	64.3	0.296	90.8	2.22
2.7	0.503	-94.8	10.511	156.6	0.015	67.9	0.306	86.7	2.29
2.8	0.489	-97.6	10.126	148.3	0.018	85.0	0.315	79.2	2.00
2.9	0.471	-101.3	9.850	143.2	0.019	993.7	0.330	73.0	1.96
3.0	0.457	-106.7	9.242	135.5	0.022	100.0	0.343	67.0	1.81
3.1	0.455	-111.3	9.065	128.9	0.026	108.0	0.357	60.7	1.53

PIN DESCRIPTIONS

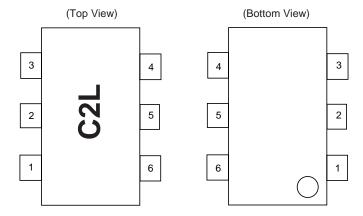
Pin No.	Symbol	Applied Voltage	Description	Internal Equivalent Circuit
1	Input	_	RF signal input pin. An internal matching circuit, configured with resistors, improves match to 50 Ω over a wide band. A multi-feedback circuit is incorporated to minimize variations in hFE and resistance values.	
2 3 5	GND	0	Ground pins. From the ground pattern as large as possible to minimize ground impedance.	
4	Output	4.5 to 5.5	RF signal output pin. Connect an inductor between this pin and Vcc to supply current to the internal output transistors.	
6	Vcc		Power supply pin. This pin biases the internal input transistor.	

OUTLINE DIMENSIONS (Units in mm)

2.0±0.2 2.0±0.2 0.65 3 1.3 0.65 2 0.9 ± 0.1 0.7 0.05 0.05 0 0.

Note: All dimensions are typical unless otherwise specified.

LEAD CONNECTIONS



- 1. INPUT
- 2. GND
- 3. GND4. OUTPUT
- 5. GND
- 6. Vcc

Note: Package Marking C2L: UPC2776TB

Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

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Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices		
Lead (Pb)	< 1000 PPM	-A Not Detected	-AZ (*)	
Mercury	< 1000 PPM	Not Detected		
Cadmium	< 100 PPM	Not Detected		
Hexavalent Chromium	< 1000 PPM	Not Detected		
PBB	< 1000 PPM	Not De	etected	
PBDE	< 1000 PPM	Not Detected		

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